



10/787121

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PTO/SB/17 (12-04v2)

Approved for use through 7/31/2006. OMB 0651-0032
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no person are required to respond to a collection of information unless it displays a valid OMB control number.

Effective on 12/08/2004. Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818).		Complete if Known	
FEE TRANSMITTAL For FY 2005		Application Number	Patent#: 6,953,720
		Filing Date	Issued: October 11, 2005
		First Named Inventor	John T. Moore
		Examiner Name	H. J. Tsai
		Art Unit	2812
<input type="checkbox"/> Applicant claims small entity status. See 37 CFR 1.27		Attorney Docket No.	M4065.0564/P564-A
TOTAL AMOUNT OF PAYMENT	(\$) 100.00		

METHOD OF PAYMENT (check all that apply)

☐ Check ☒ Credit Card ☐ Money Order ☐ None ☐ Other (please identify): _____

☐ Deposit Account Deposit Account Number: 04-1073 Deposit Account Name: Dickstein Shapiro Morin & Oshinsky LLP

For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)

☒ Charge fee(s) indicated below ☐ Charge fee(s) indicated below, except for the filing fee

☐ Charge any additional fee(s) or underpayment of fee(s) under 37 CFR 1.16 and 1.17 ☒ Credit any overpayments

FEE CALCULATION

1. BASIC FILING, SEARCH, AND EXAMINATION FEES

Application Type	FILING FEES		SEARCH FEES		EXAMINATION FEES		Fees Paid (\$)
	Fee (\$)	Small Entity Fee (\$)	Fee (\$)	Small Entity Fee (\$)	Fee (\$)	Small Entity Fee (\$)	
Utility	300	150	500	250	200	100	
Design	200	100	100	50	130	65	
Plant	200	100	300	150	160	80	
Reissue	300	150	500	250	600	300	
Provisional	200	100	0			0	

2. EXCESS CLAIM FEES

Fee Description	Small Entity	
	Fee (\$)	Fee (\$)
Each claim over 20 (including Reissues)	50	25
Each independent claim over 3 (including Reissues)	200	100
Multiple dependent claims	360	180

3. APPLICATION SIZE FEE

If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).

Total Sheets	Extra Sheets	Number of each additional 50 or fraction thereof	Fee (\$)	Fee Paid (\$)
_____	_____	_____	_____	_____

4. OTHER FEE(S)

	Fees Paid (\$)
Non-English Specification, \$130 fee (no small entity discount)	
Other (e.g., late filing surcharge): <u>1811 Certificate of correction</u>	100.00

SUBMITTED BY		Registration No.	Telephone
Signature		(Attorney/Agent) 28,371	(202) 828-2232
Name (Print/Type)	Thomas J. D'Amico	Date	January 6, 2006

JAN 11 2006

JAN 11 2006



Docket No.: M4065.0564/P564-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
John T. Moore et al.

Patent No.: 6,953,720

Issued: October 11, 2005

For: METHODS FOR FORMING
CHALCOGENIDE GLASS-BASED
MEMORY ELEMENTS

REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 CFR 1.322 & 1.323

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted omissions and typographical errors which should be corrected.

In the U.S. Patent Documents portion of the Reference Cited section, the following patent was omitted by the PTO and should be added (Exhibit A, attached, lists this patent):

6,707,712

3/2004

Lowery

01/09/2006 JADD01 00000000 6953720
01 FC:1811 100.00 DP

JAN 11 2006

In the Other Publications portion of the References Cited section, the PTO omitted the following two references which should be added (Exhibit B, attached, lists these publications:

Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936.; and

Thornburg, D.D., Memory switching in amorphous arsenic triselenide, J. Non-Cryst. Solids 11 (1972) 113-120.

In the Other Publications portion of the References Cited section, the PTO made the following errors which should be corrected:

"Bernede, J.C. Polarized memory switching in MIS thin films, Thin Solid Films 87 (1981) 155-160."

Should Read

--Bernede, J.C. Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.--;

"Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, J. Non-Cryst. Solids 222 (1997) 134-143."

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--Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, J. Non-Cryst. Solids 222 (1997) 137-143.--;

"Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=NI, BI), Mat. Chem, And Physics 28 (1991) 253-258."

Should read

--Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem, And Physics 28 (1991) 253-258.--; and

"Snell, A.J.; Hajto, J.; Rosa, M.J.; Osborne, L.S.; Holmes, A.; Owen, A.E.; Gibson, R.A.G., Analogue memory effects in metal/a -Si:H/metal thin films structures, Mat. Res. Soc. Symp. Proc. V 297, 1993, 1017-1021."

Should read

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In the Other Publications portion of the References Cited section, Applicants made the following error which should be corrected:

"Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a -Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080"

Should read

--Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in metal/a -Si:H/metal memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.--.

In the Specification, Applicants made the following error to be corrected:

Column 3, line 56, "to second" should read --to a second--.

In the Specification, the PTO made the following error to be corrected:

Column 7, line 63, "carried Out" should read --carried out--.

The errors were made primarily by the PTO with just two found in the application as filed by Applicants. Please charge our Credit Card in the amount of

\$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed.

The errors now sought to be corrected are inadvertent omissions and typographical errors the correction of which does not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentees respectfully solicit the granting of the requested Certificate of Correction.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0564/P564-A.

Dated: January 6, 2006

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

Elizabeth Parsons

Registration No.: 52,499

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Attorneys for Applicants

JAN 11 2006



Exhibit A

JAN 11 2006



INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Complete If Known

Application Number	10/787,121
Filing Date	February 27, 2004
First Named Inventor	John T. Moore
Art Unit	2812
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4066.0564/P564-A

Sheet	3	of	3
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U	R3	US 6,646,297	11/2003	Dennison	X
	S3	US 6,649,928	11/2003	Dennison	
	T3	US 6,687,900	12/2003	Lowery et al.	
	U3	US 6,671,710	12/2003	Ovshinsky et al.	
	V3	US 6,673,648	1/2004	Lowrey	
	W3	US 6,673,700	1/2004	Dennison et al.	
	X3	US 6,674,115	1/2004	Hudgens et al.	
	Y3	US 6,687,427	2/2004	Ramalingam et al.	
	Z3	US 6,690,026	2/2004	Peterson	
	A4	US 6,696,355	2/2004	Dennison	
W	B4	US 6,687,153	2/2004	Lowery	X
	C4	US 6,707,712	3/2004	Lowery	
	D4	US 6,714,954	3/2004	Ovshinsky et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	To
		Country Code ² -Number ³ -Kind Code ⁴ (if known)				

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinda Codes of USPTO Patent Documents at www.uspto.gov or MPEP 801.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language translation is attached.

NON PATENT LITERATURE DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

***EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

A-Jay Tsoni 5/4/05

JAN 11 2006



Exhibit B

JAN 11 2006



PTO/SB/08B (10-01)

Approved for use through 10/31/2002.OMB 0651-0031

U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449B/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet	3	of	8	Application Number	Not Yet Assigned
				Filing Date	March 1, 2004
				First Named Inventor	John T. Moore
				Group Art Unit	Not Yet Assigned
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	M4065.0564/P564-A

		Glasses, Asian Journal of Physics (2000) 9, 709-72. **	
m	CX	Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073. **	
	CY	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703 **	
	CZ	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132. **	
	CA1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420. **	
	CB1	Boolchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe2 glass, Phys. Rev. B 25 (1982) 2975-2978. **	
	CC1	Boolchand, P.; Grothaus, J.; Phillips, J.C., Broken chemical order and phase separation in GexSe1-x glasses, Solid state comm. 45 (1983) 183-185. **	
	CD1	Boolchand, P.; Bresser, W.J., Compositional trends in glass transition temperature (Tg), network connectivity and nanoscale chemical phase separation in chalcogenides, Dept. of ECECS, Univ. Cincinnati (October 28, 1999) 45221-0030. **	
	CE1	Boolchand, P.; Grothaus, J., Molecular Structure of Melt-Quenched GeSe2 and GeS2 glasses compared, Proc. Int. Conf. Phys. Semicond. (Eds. Chadi and Harrison) 17 th (1985) 833-36. **	
	CF1	Bresser, W.; Boolchand, P.; Suranyi, P., Rigidity percolation and molecular clustering in network glasses, Phys. Rev. Lett. 56 (1986) 2493-2496. **	
	CG1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; de Neufville, J.P., Intrinsically broken chalcogen chemical order in stoichiometric glasses, Journal de Physique 42 (1981) C4-193-C4-196. **	
	CH1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; Hernandez, J.G., Molecular phase separation and cluster size in GeSe2 glass, Hyperfine Interactions 27 (1986) 389-392. **	
	CI1	Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chemyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe2 Crystals, Science 258 (1992) 271-274. **	
	CJ1	Chatterjee, R.; Asokan, S.; Titus, S.S.K., Current-controlled negative-resistance behavior and memory switching in bulk As-Te-Se glasses, J. Phys. D: Appl. Phys. 27 (1994) 2624-2627. **	
	CK1	Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy GexSe1-x films, Appl. Phys. Lett. 37 (1980) 1075-1077. **	
*	CL1	Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936. **	
	CM1	Chen, G.; Cheng, J.; Chen, W., Effect of Si3N4 on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253. **	
	CN1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891. **	
	CO1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786. **	
	CP1	Daiven, R.; Gill, R., Electrical properties of beta-Ag2Te and beta-Ag2Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756. **	
	CQ1	Davis, E.A., Semiconductors without form, Search 1 (1970) 152-155. **	
	CR1	Deamaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191. **	
	CS1	Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 182-180. **	
	CT1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813. **	
	CU1	Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous	



PTO/SB/08B (10-01)

Approved for use through 10/31/2002. OMB 0851-0031

U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete If Known

Application Number	Not Yet Assigned 10/787/121
Filing Date	March 1, 2004
First Named Inventor	John T. Moore
Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4085.0564/P564-A

Sheet 8 of 8

		1373-1377. **	
	CM5	Tanaka, K.; Ilizma, S.; Sugl, M.; Okada, Y.; Kikuchi, M., Thermal effects on switching phenomenon in chalcogenide amorphous semiconductors, Solid State Comm. 8 (1970) 387-389. **	
	CN5	Thornburg, D.D., Memory switching in a Type I amorphous chalcogenide, J. Elect. Mat. 2 (1973) 3-15. **	
*	CO5	Thornburg, D.D., Memory switching in amorphous arsenic triselenide, J. Non-Cryst. Solids 11 (1972) 113-120. **	
	CP5	Thornburg, D.D.; White, R.M., Electric field enhanced phase separation and memory switching in amorphous arsenic triselenide, Journal(?) (1972) 4609-4612. **	
	CQ5	Tichy, L.; Ticha, H., Remark on the glass-forming ability in GexSe1-x and AsxSe1-x systems, J. Non-Cryst. Solids 261 (2000) 277-281. **	
	CR5	Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1993) 14650-14652. **	
	CS5	Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium. 9-13 September 1985. **	
	CT5	Tregouet, Y.; Bernede, J.C., Silver movements in Ag2Te thin films: switching and memory effects, Thin Solid Films 57 (1979) 49-54. **	
	CU5	Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally induced crystallization of amorphous Ge0.4Se0.6, J. Non-Cryst. Solids 117-118 (1990) 219-221. **	
	CV5	Uttecht, R.; Stevenson, H.; Sie, C.H.; Griener, J.D.; Raghavan, K.S., Electric field induced filament formation in As-Te-Ge glass, J. Non-Cryst. Solids 2 (1970) 358-370. **	
	CD5	Viger, C.; Lefrancols, G.; Fleury, G., Anomalous behaviour of amorphous selenium films, J. Non-Cryst. Solids 33 (1976) 267-272. **	
	CX5	Vodenicharov, C.; Parvanov, S.; Petkov, P., Electrode-limited currents in the thin-film M-GeSe-M system, Mat. Chem. And Phys. 21 (1989) 447-454. **	
	CY5	Wang, S.-J.; Misium, G.R.; Camp, J.C.; Chen, K.-L.; Tigelaar, H.L., High-performance Metal/silicide antifuse, IEEE electron dev. Lett. 13 (1992) 471-472. **	
	CZ5	Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73. **	
	CA6	West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the Ag[As0.24S0.36Ag0.40]Ag System prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974. **	
	CB6	West, W.C., Electrically erasable non-volatile memory via electrochemical deposition of multifractal aggregates, Ph.D. Dissertation, ASU 1998. **	
	CC6	Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, Tg, with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the slope [dTg/d<m>] at the rigidity percolation threshold (<m>=2.4), J. Non-Cryst. Solids 151 (1992) 149-154. **	

Examiner Signature	A-Jay [Signature]	Date Considered	8/2/05
--------------------	-------------------	-----------------	--------

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¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

JAN 11 2006

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 2

PATENT NO. : 6,953,720
APPLICATION NO. : 10/787,121
ISSUE DATE : October 11, 2005
INVENTOR(S) : John T. Moore et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the U.S. Patent Documents portion of the Reference Cited section, the following patent is added:

6,707,712 3/2004 Lowery

In the Other Publications portion of the References Cited section, the following two references are added:

Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936.; and

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Should Read

--Bernede, J.C. Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.--;

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 1
2101 L Street NW
Washington, DC 20037-1526

JAN 11 2006

"Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, J. Non-Cryst. Solids 222 (1997) 134-143."

Should read

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Should read

--Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem. And Physics 28 (1991) 253-258.--;

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"Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a -Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080"

Should read

--Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in metal/a -Si:H/metal memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.--.

In the Specification, the following errors are corrected:

Column 3, line 56, "to second" should read --to a second--; and

Column 7, line 63, "carried Out" should read --carried out--.

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 2
2101 L Street NW
Washington, DC 20037-1526

JAN 11 2006